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(54) Title: LOW-COST SUBSTRATES HAVING HIGH-RESISTIVITY PROPERTIES AND METHODS FOR THEIR MANUFACTURE

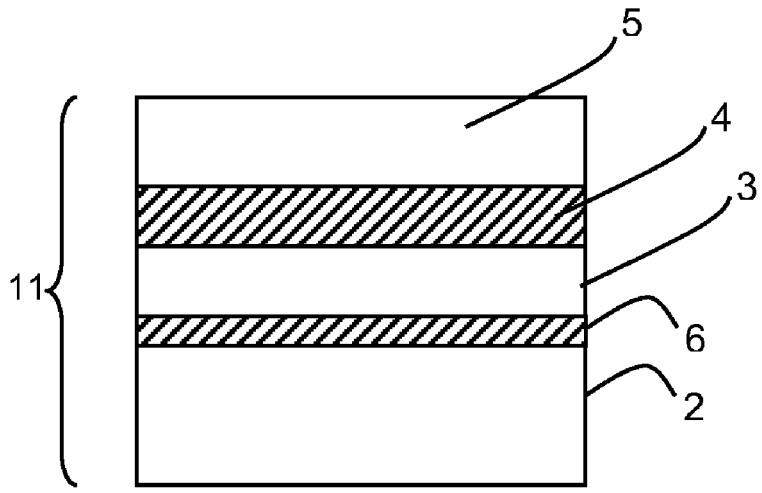


Figure 2

(57) Abstract: In one embodiment, the invention provides substrates that are structured so that devices fabricated in a top layer thereof have properties similar to the same devices fabricated in a standard high resistivity substrate. Substrates of the invention include a support having a standard resistivity, a semiconductor layer arranged on the support substrate having a high-resistivity, preferably greater than about 1000 Ohms-cm, an insulating layer arranged on the high-resistivity layer, and a top layer arranged on the insulating layer. The invention also provides methods for manufacturing such substrates.

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